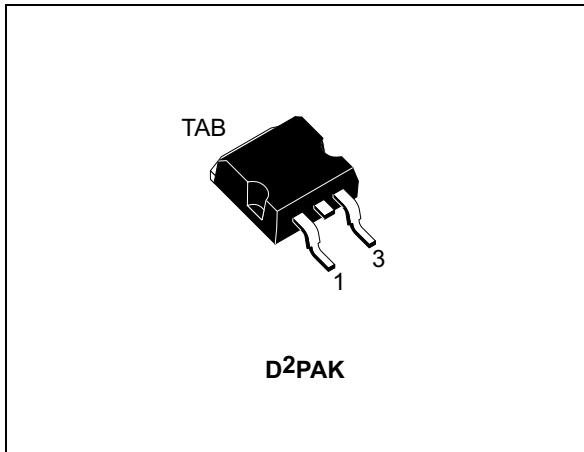


## N-channel 60 V, 4.7 mΩ typ., 100 A STripFET™ F7 Power MOSFET in a D<sup>2</sup>PAK package

Datasheet - production data



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STB100N6F7	60 V	5.6 mΩ	100A	125 W

- Among the lowest R<sub>DS(on)</sub> on the market
- Excellent figure of merit (FoM)
- Low C<sub>rss</sub>/C<sub>iss</sub> ratio for EMI immunity
- High avalanche ruggedness

### Applications

- Switching applications

### Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Figure 1. Internal schematic diagram

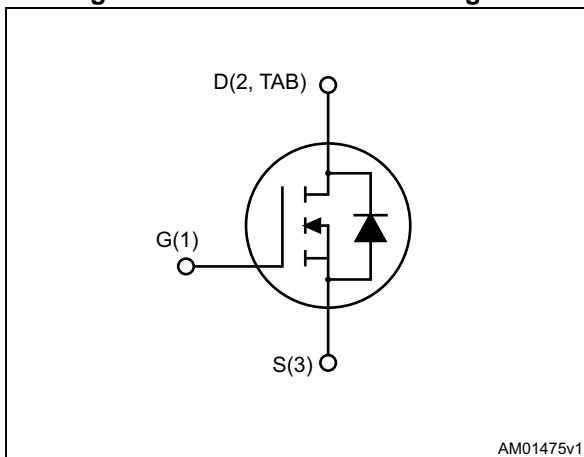


Table 1. Device summary

Order code	Marking	Package	Packaging
STB100N6F7	100N6F7	D <sup>2</sup> PAK	Tape and Reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>8</b>
<b>4</b>	<b>Package information</b> .....	<b>9</b>
<b>5</b>	<b>Packing information</b> .....	<b>12</b>
<b>6</b>	<b>Revision history</b> .....	<b>14</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	100	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	75	A
$I_{DM}^{(1)}$	Drain current (pulsed)	400	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	125	W
$E_{AS}^{(2)}$	Single pulse avalanche energy	200	mJ
$T_j$	Operating junction temperature	- 55 to 175	$^\circ\text{C}$
$T_{stg}$	Storage temperature		

1. Pulse width is limited by safe operating area

2. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 20\text{ A}$ ,  $V_{DD} = 30\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.2	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	thermal resistance junction-pcb	35	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	60			V
$I_{DSS}$	Zero gate voltage Drain current	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}, T_J = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		4.7	5.6	m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	1980	-	pF
$C_{oss}$	Output capacitance		-	970	-	pF
$C_{riss}$	Reverse transfer capacitance		-	86	-	pF
$Q_g$	Total gate charge	$V_{DD} = 30\text{ V}, I_D = 100\text{ A}, V_{GS} = 10\text{ V}$	-	30	-	nC
$Q_{gs}$	Gate-source charge		-	12.6	-	nC
$Q_{gd}$	Gate-drain charge		-	5.9	-	nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}, I_D = 50\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$	-	21.6	-	ns
$t_r$	Rise time		-	55.5	-	ns
$t_{d(off)}$	Turn-off-delay time		-	28.6	-	ns
$t_f$	Fall time		-	15	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 100 \text{ A}$	-		1.2	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 100 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 48 \text{ V}$	-	48.4		ns
$Q_{rr}$	Reverse recovery charge		-	47		nC
$I_{RRM}$	Reverse recovery current		-	2.0		A

1. Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

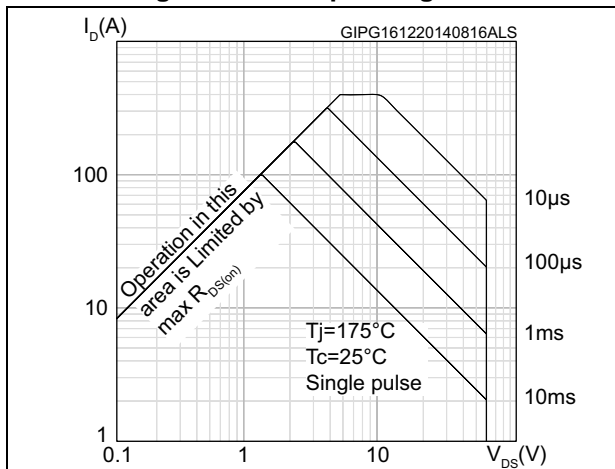


Figure 3. Thermal impedance

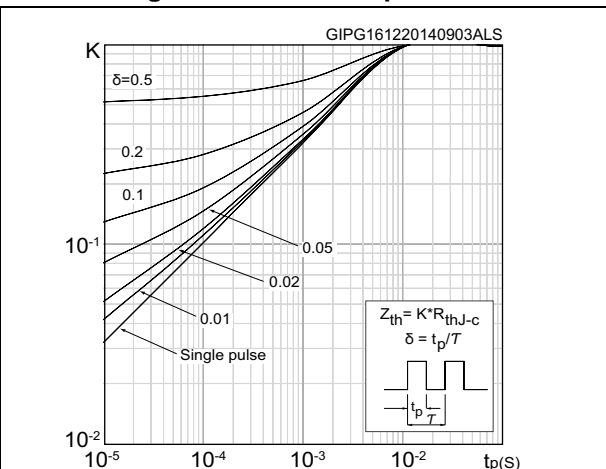


Figure 4. Output characteristics

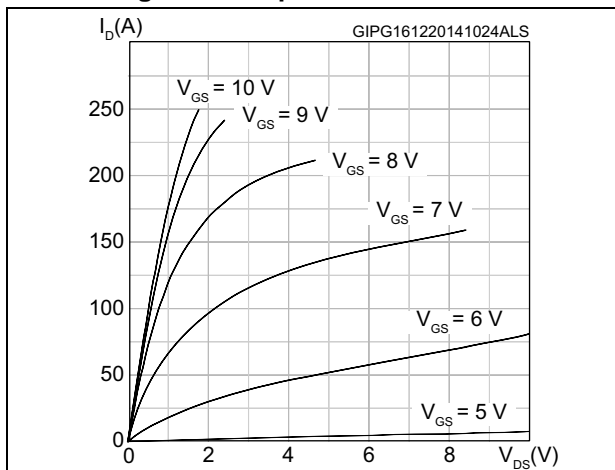


Figure 5. Transfer characteristics

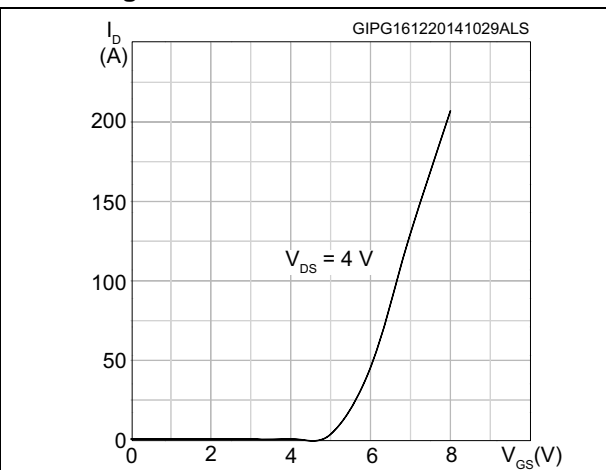


Figure 6. Gate charge vs gate-source voltage

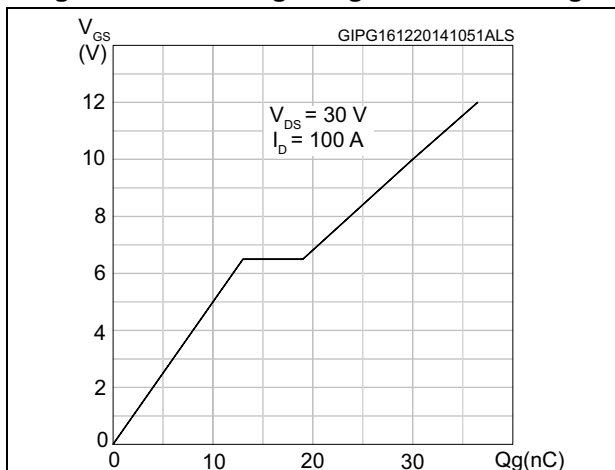


Figure 7. Static drain-source on-resistance

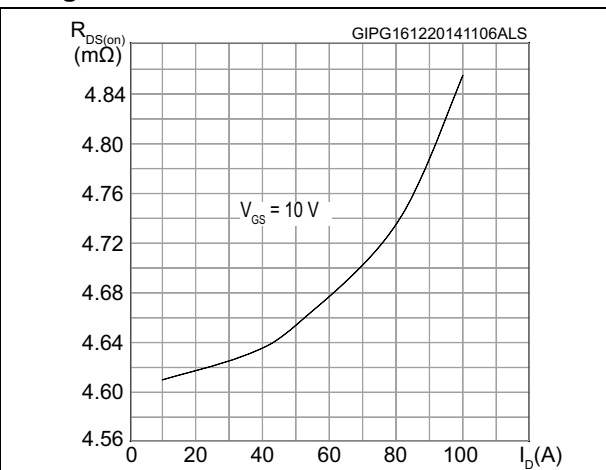


Figure 8. Capacitance variations

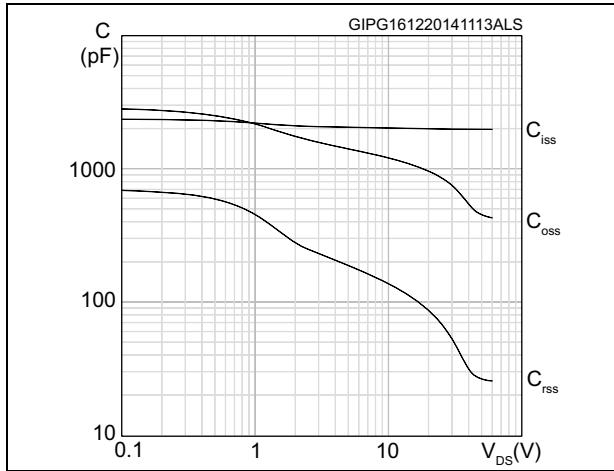


Figure 9. Normalized gate threshold voltage vs temperature

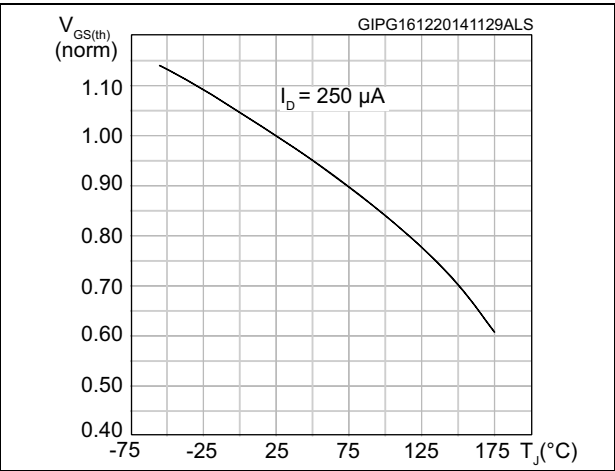


Figure 10. Normalized on-resistance vs temperature

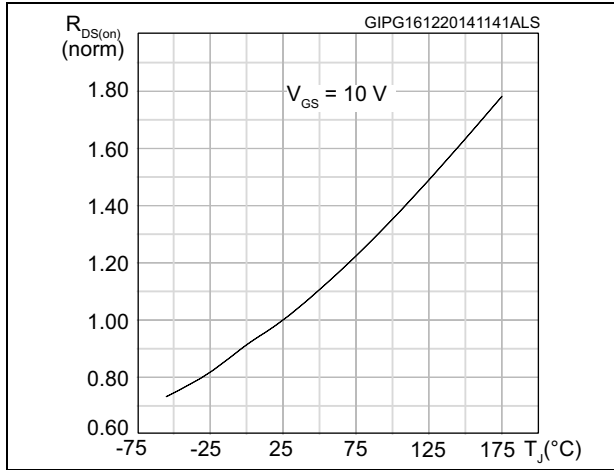


Figure 11. Source-drain diode forward characteristics

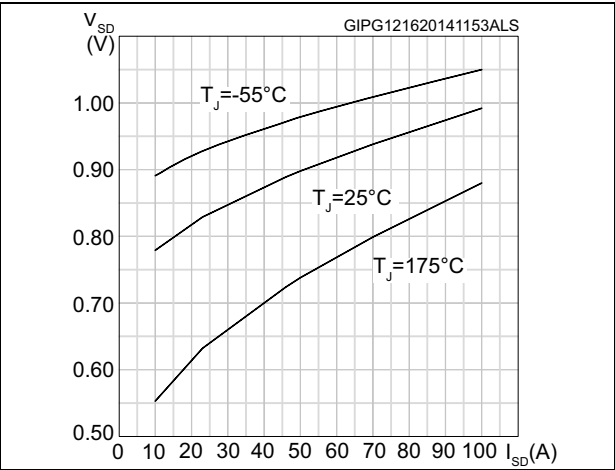
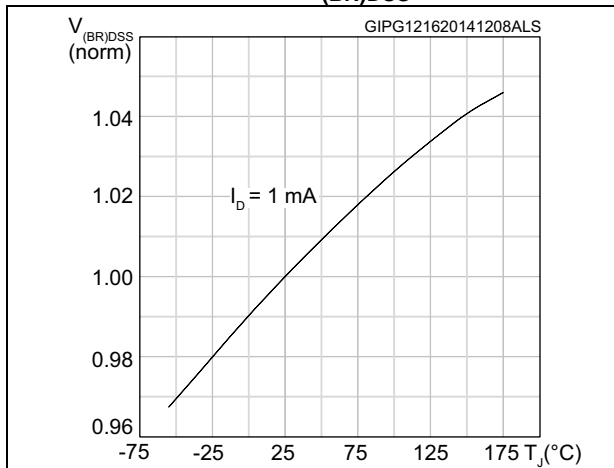
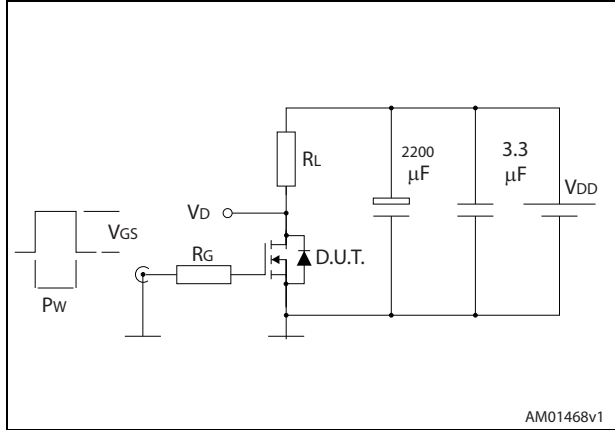


Figure 12. Normalized  $V_{(BR)DSS}$  vs temperature

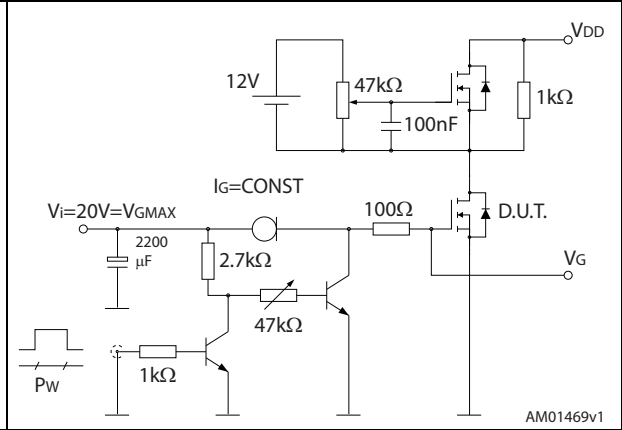


### 3 Test circuits

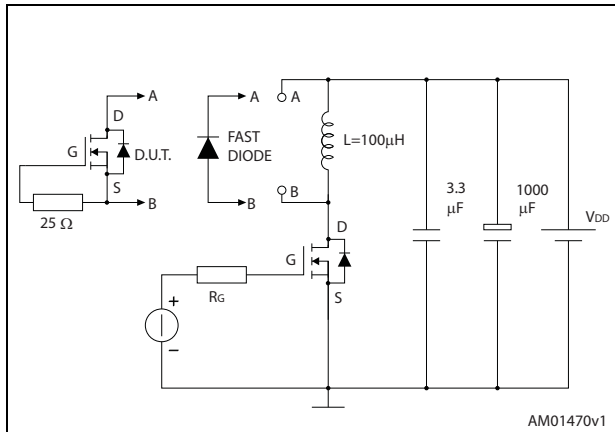
**Figure 13. Switching times test circuit for resistive load**



**Figure 14. Gate charge test circuit**



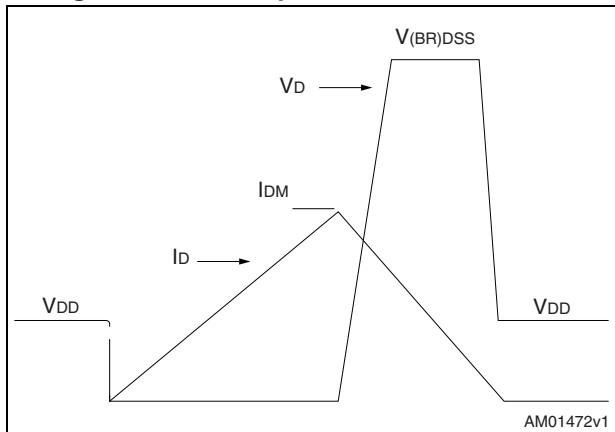
**Figure 15. Test circuit for inductive load switching and diode recovery times**



**Figure 16. Unclamped inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 19. D<sup>2</sup>PAK (TO-263) package outline

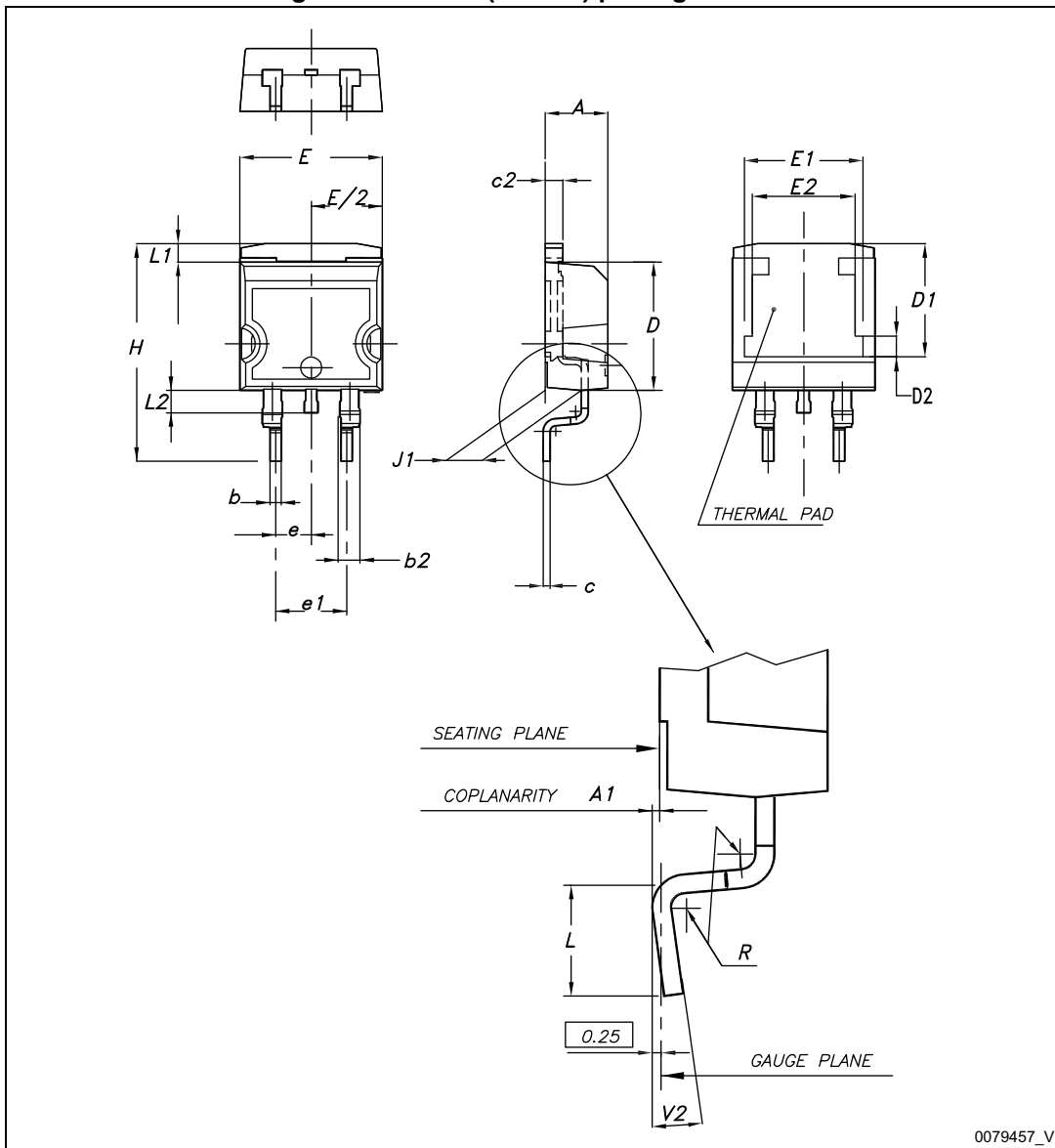
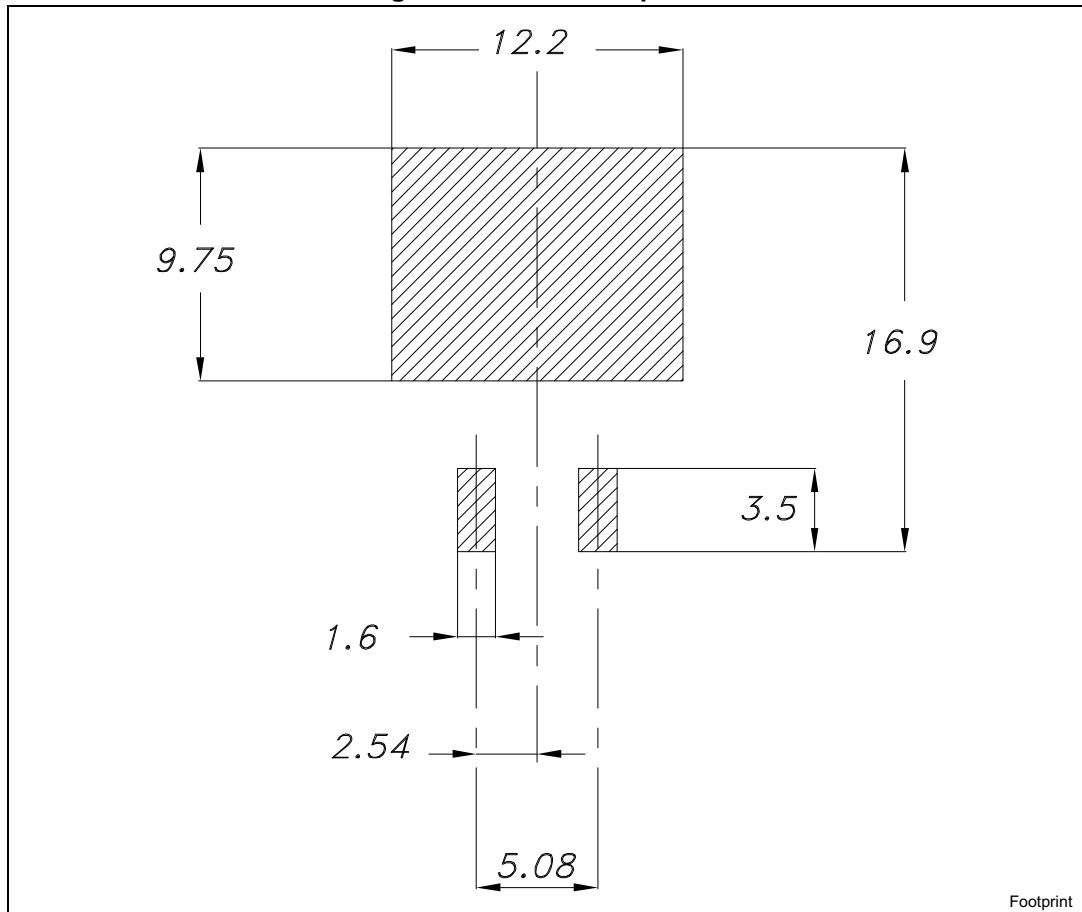


Table 8. D<sup>2</sup>PAK (TO-263) package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

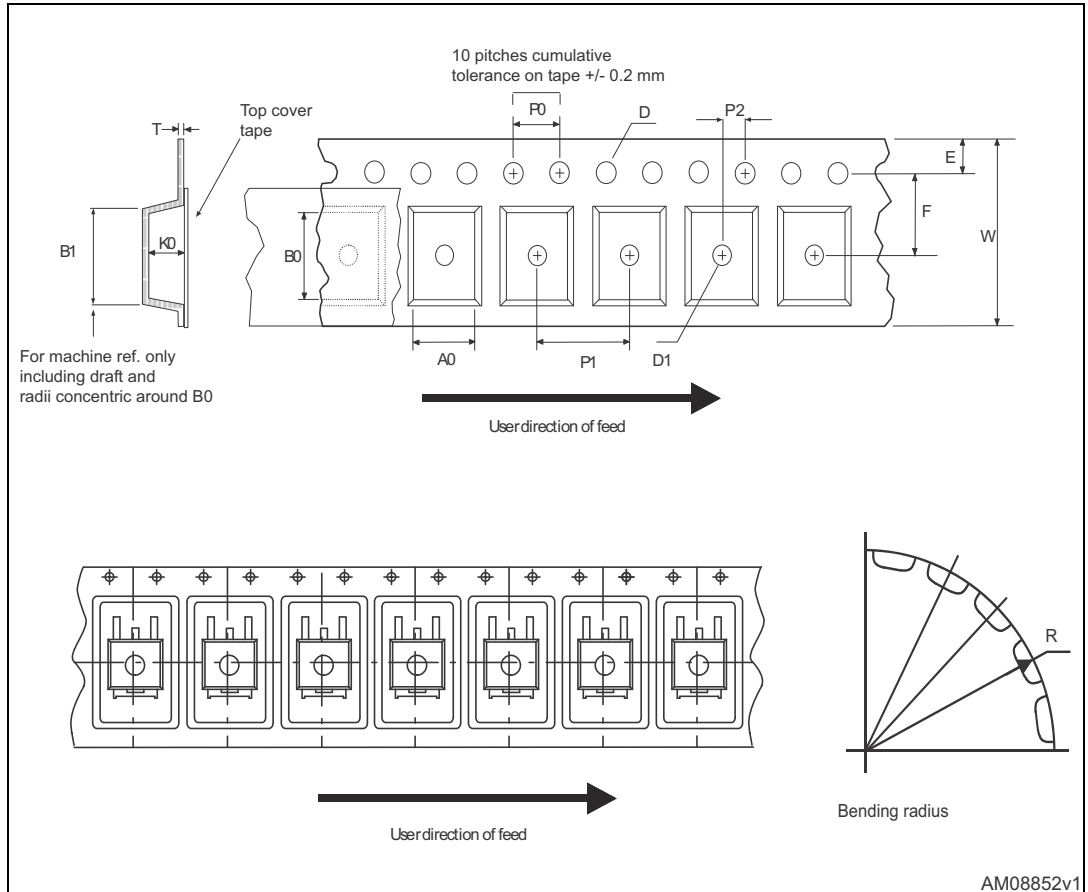
Figure 20. D<sup>2</sup>PAK footprint<sup>(a)</sup>



a. All dimension are in millimeters

# 5 Packing information

Figure 21. Tape





## 6 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
26-Nov-2014	1	First release.
14-Jan-2015	2	Text amendments throughout document On cover page: Changed title description Changed features and descriptions Updated Table 2: Absolute maximum ratings Updated Table 4: On/off states Updated Table 5: Dynamic Updated Table 6: Switching times Updated Table 7: Source drain diode Added Section 2.1: Electrical characteristics (curves) Updated Section 4: Package mechanical data
15-Dec-2015	3	Updated <a href="#">Table 3: Thermal data</a> . Minor text changes.

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